

MOSFET – N-Channel, QFET

800 V, 3.0 A, 4.8 mΩ

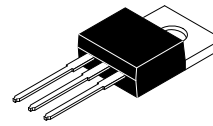
FQP3N80C, FQPF3N80C

Description

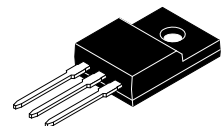
This N-Channel enhancement mode power MOSFET is produced using onsemi's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power factor correction (PFC), and electronic lamp ballasts.

Features

- 3.0 A, 800 V, $R_{DS(on)} = 4.8 \Omega$ (Max.) @ $V_{GS} = 10$ V, $I_D = 1.5$ A
- Low Gate Charge (Typ. 13 nC)
- Low C_{RSS} (Typ. 5.5 pF)
- 100% Avalanche Tested

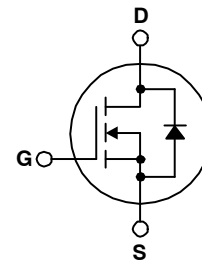


TO-220-3LD
CASE 340AT

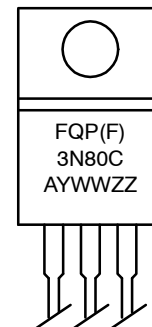


TO-220 Fullpack,
3-Lead /
TO-220F-3SG
CASE 221AT

N-CHANNEL MOSFET



MARKING DIAGRAM



FQP(F)3N80C	= Specific Device Code
A	= Assembly Location
YWW	= Date Code (Year & Week)
ZZ	= Assembly Lot

ORDERING INFORMATION

Device	Package	Shipping
FQP3N80C	TO-220-3LD	1,000 Units / Tube
FQPF3N80C	TO-220 Fullpack	1,000 Units / Tube

FQP3N80C, FQPF3N80C

MOSFET MAXIMUM RATINGS (T_C = 25°C unless otherwise noted)

Symbol	Parameter	FQP3N80C	FQPF3N80C	Unit
V _{DSS}	Drain–Source Voltage	800	800	V
I _D	Drain Current	3 1.9	3* 1.9*	A A
I _{DM}	Drain Current	12	12*	A
V _{GSS}	Gate–Source Voltage	±30	±30	V
E _{AS}	Single Pulsed Avalanche Energy (Note 2)	320	320	mJ
I _{AR}	Avalanche Current (Note 1)	3	3	A
E _{AR}	Repetitive Avalanche Energy (Note 1)	10.7	10.7	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	4.5	4.5	V/ns
P _D	Power Dissipation	107 0.85	39 0.31	W W/°C
T _J , T _{STG}	Operating and Storage Temperature Range	–55 to +150	–55 to +150	°C
T _L	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds	300	300	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Symbol	Parameter	FQP3N80C	FQPF3N80C	Unit
R _{θJC}	Thermal Resistance, Junction–to–Case, Max.	1.17	3.2	°C/W
R _{θJA}	Thermal Resistance, Junction–to–Ambient, Max.	62.5	62.5	°C/W

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

BV _{DSS}	Drain–Source Breakdown Voltage	V _{GS} = 0 V, I _D = 250 μA	800	–	–	V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	I _D = 250 μA, Referenced to 25°C	–	1	–	V/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 800 V, V _{GS} = 0 V V _{DS} = 640 V, T _C = 125°C	– –	– –	10 100	μA μA
I _{GSSF}	Gate–Body Leakage Current, Forward	V _{GS} = 30 V, V _{DS} = 0 V	–	–	100	nA
I _{GSSR}	Gate–Body Leakage Current, Reverse	V _{GS} = –30 V, V _{DS} = 0V	–	–	–100	nA

ON CHARACTERISTICS

V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250 μA	3.0	–	5.0	V
R _{DS(on)}	Static Drain–Source On–Resistance	V _{GS} = 10 V, I _D = 1.5 A	–	4.0	4.8	Ω
g _{FS}	Forward Transconductance	V _{DS} = 50 V, I _D = 1.5 A	–	3	–	S

DYNAMIC CHARACTERISTICS

C _{iss}	Input Capacitance	V _{DS} = 25 V, V _{GS} = 0 V, f = 1.0 MHz	–	543	705	pF
C _{oss}	Output Capacitance		–	54	70	pF
C _{rss}	Reverse Transfer Capacitance		–	5.5	7.5	pF

FQP3N80C, FQPF3N80C

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted)(continued)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
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SWITCHING CHARACTERISTICS

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 400\text{ V}$, $I_D = 3\text{ A}$, $R_G = 25\ \Omega$ (Note 4)	–	15	40	ns
t_r	Turn-On Rise Time		–	43.5	95	ns
$t_{d(off)}$	Turn-Off Delay Time		–	22.5	55	ns
t_f	Turn-Off Fall Time		–	32	75	ns
Q_g	Total Gate Charge	$V_{DS} = 640\text{ V}$, $I_D = 3\text{ A}$, $V_{GS} = 10\text{ V}$ (Note 4)	–	13	16.5	nC
Q_{gs}	Gate-Source Charge		–	3.4	–	nC
Q_{gd}	Gate-Drain Charge		–	5.8	–	nC

DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS

I_S	Maximum Continuous Drain-Source Diode Forward Current		–	–	3.0	A
I_{SM}	Maximum Pulsed Drain-Source Diode Forward Current		–	–	12	A
V_{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0\text{ V}$, $I_S = 3.0\text{ A}$	–	–	1.4	V
t_{rr}	Reverse Recovery Time	$V_{GS} = 0\text{ V}$, $I_S = 3.0\text{ A}$, $di_F/dt = 100\text{ A}/\mu\text{s}$	–	642	–	ns
Q_{rr}	Reverse Recovery Charge		–	4.0	–	μC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

1. Repetitive rating; pulse-width limited by maximum junction temperature.
2. $L = 67\text{ mH}$, $I_{AS} = 3.0\text{ A}$, $V_{DD} = 50\text{ V}$, $R_G = 25\ \Omega$, starting $T_J = 25^\circ\text{C}$.
3. $I_{SD} \leq 3\text{ A}$, $di/dt \leq 200\text{ A}/\mu\text{s}$, $V_{DD} \leq BV_{DSS}$, starting $T_J = 25^\circ\text{C}$.
4. Essentially independent of operating temperature.

FQP3N80C, FQPF3N80C

TYPICAL CHARACTERISTICS

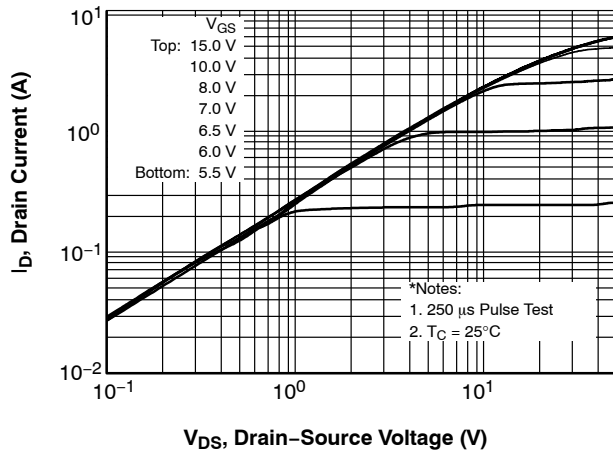


Figure 1. On-Region Characteristics

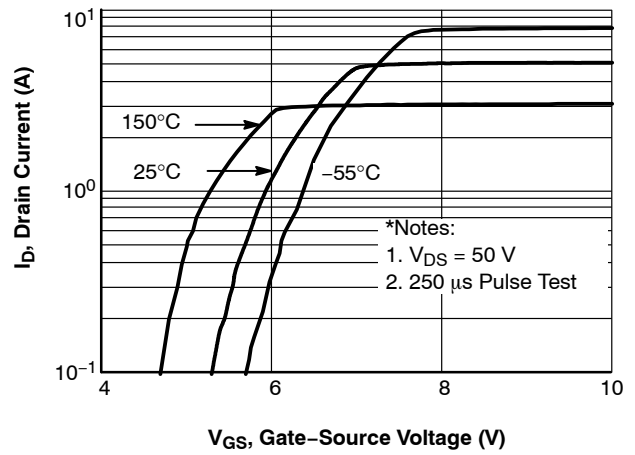


Figure 2. Transfer Characteristics

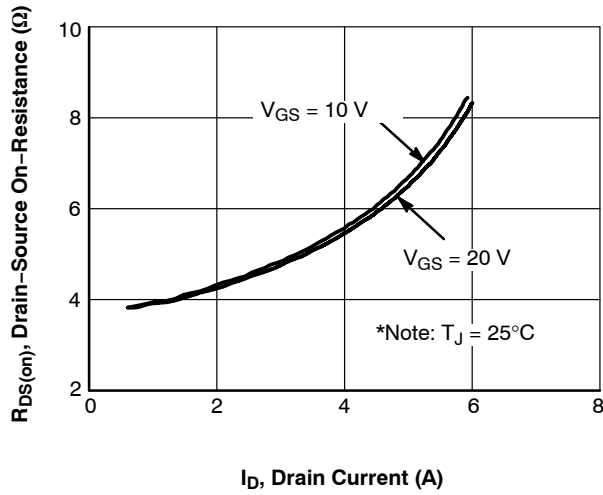


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

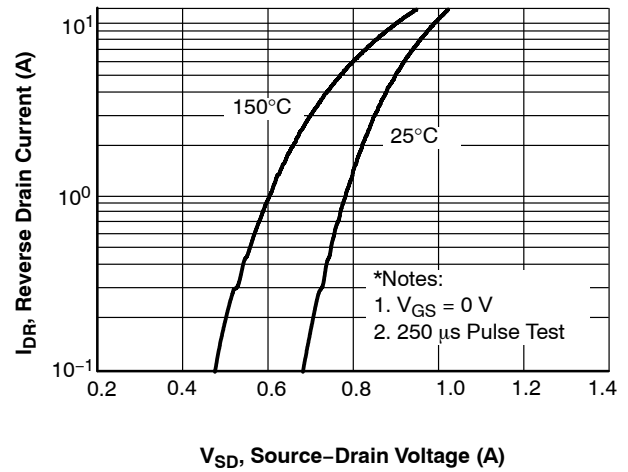


Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature

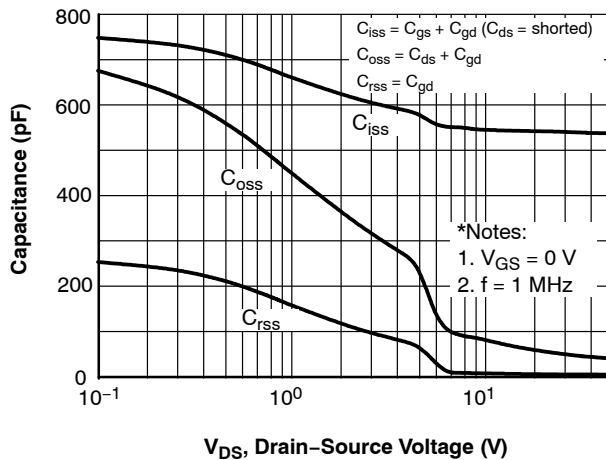


Figure 5. Capacitance Characteristics

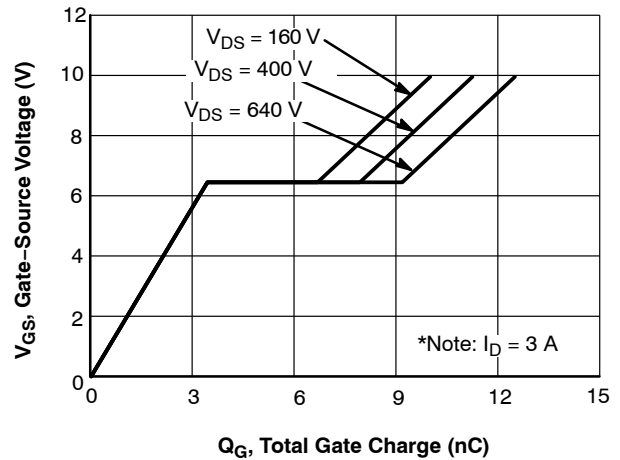


Figure 6. Gate Charge Characteristics

FQP3N80C, FQPF3N80C

TYPICAL CHARACTERISTICS (continued)

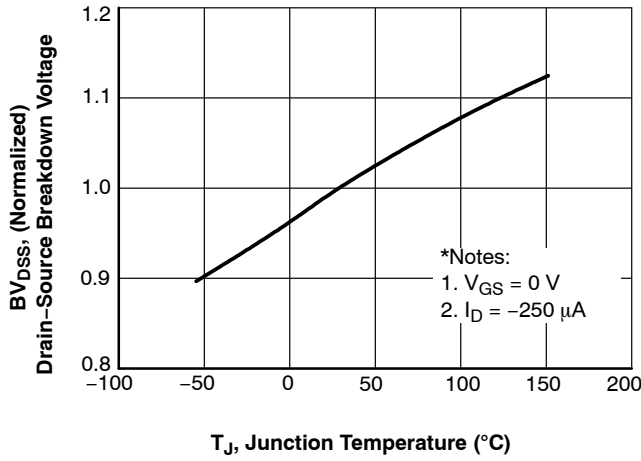


Figure 7. Breakdown Voltage Variation vs. Temperature

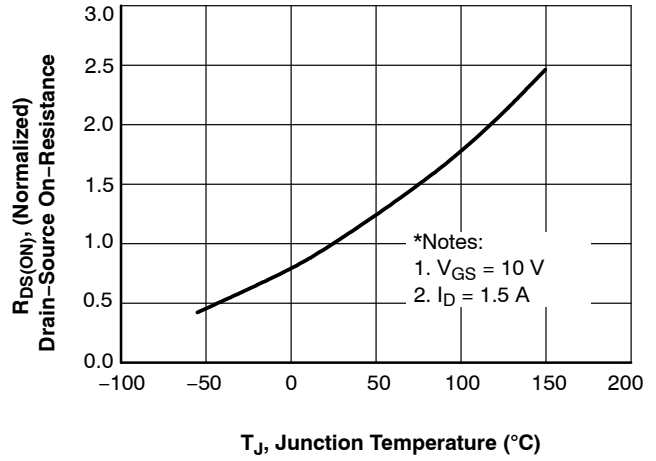


Figure 8. On-Resistance Variation vs. Temperature

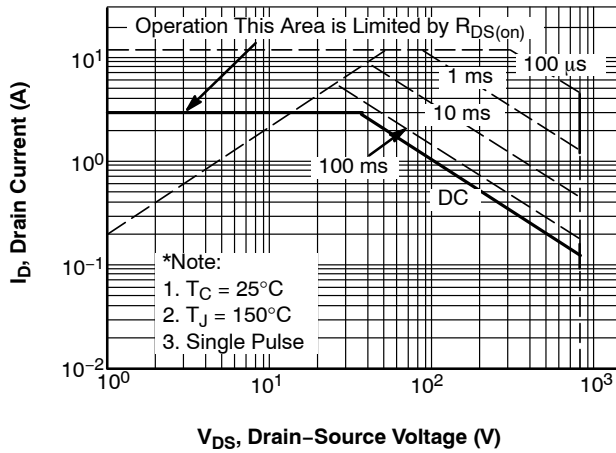


Figure 9. Maximum Safe Operating Area for FQP3N80C

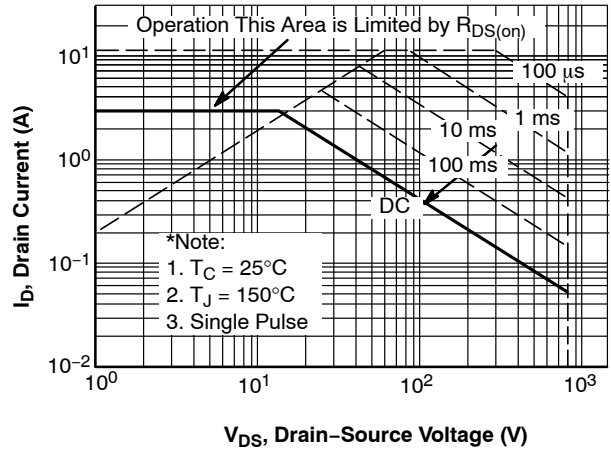


Figure 10. Maximum Safe Operating Area for FQPF3N80C

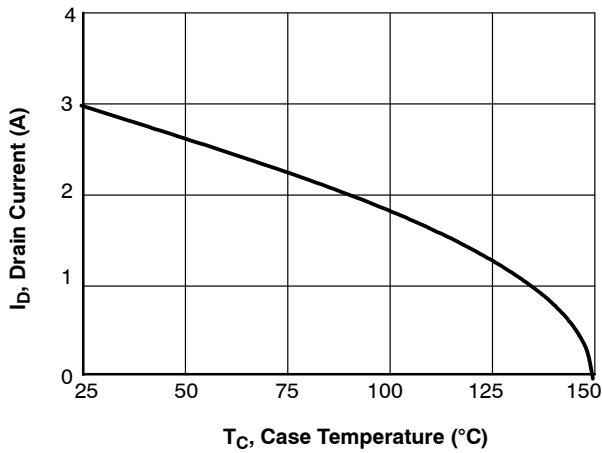


Figure 11. Maximum Drain Current vs. Case Temperature

FQP3N80C, FQPF3N80C

TYPICAL CHARACTERISTICS (continued)

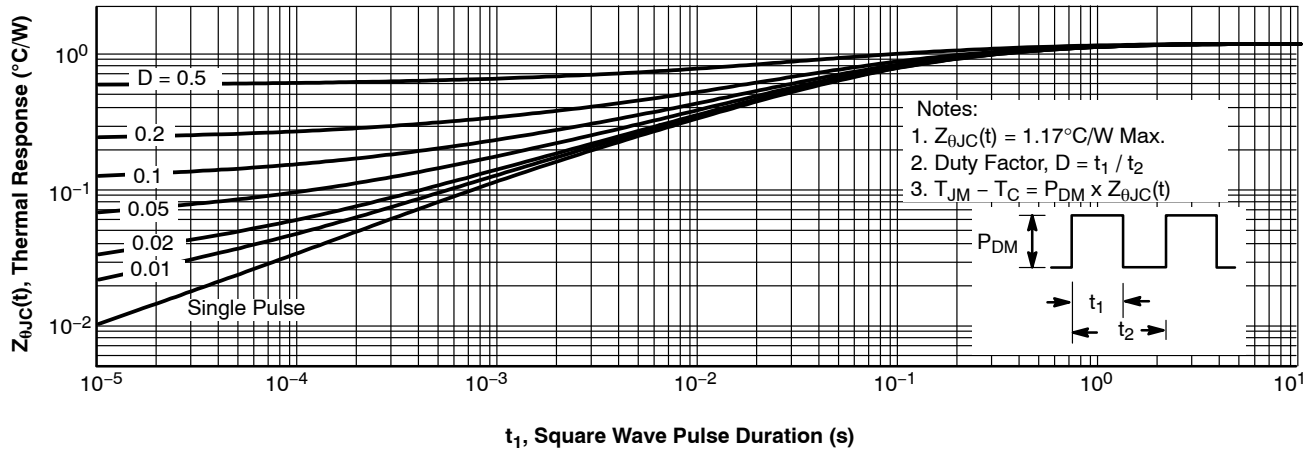


Figure 12. Transient Thermal Response Curve for FQP3N80C

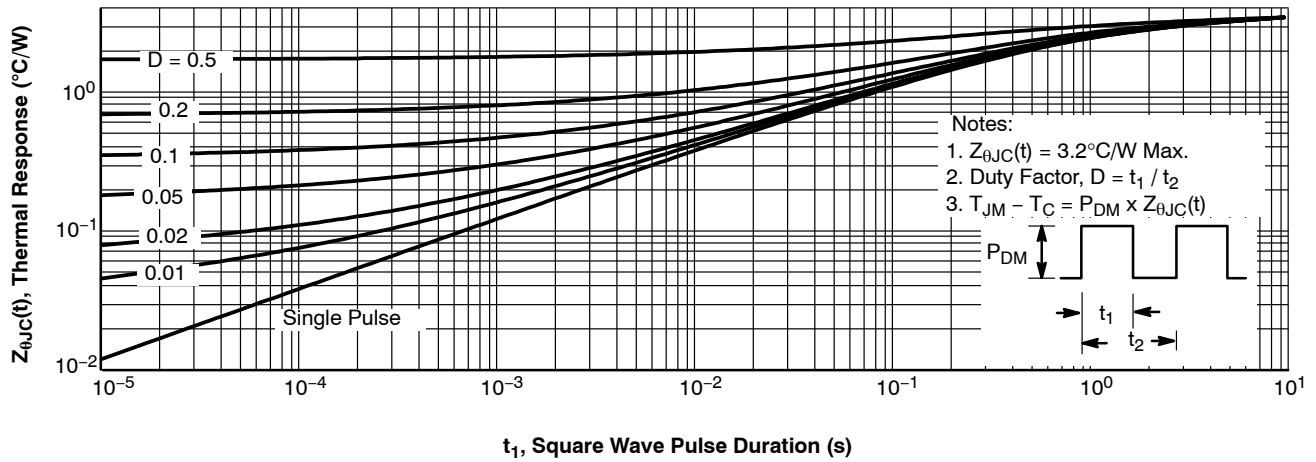


Figure 13. Transient Thermal Response Curve for FQPF3N80C

FQP3N80C, FQPF3N80C

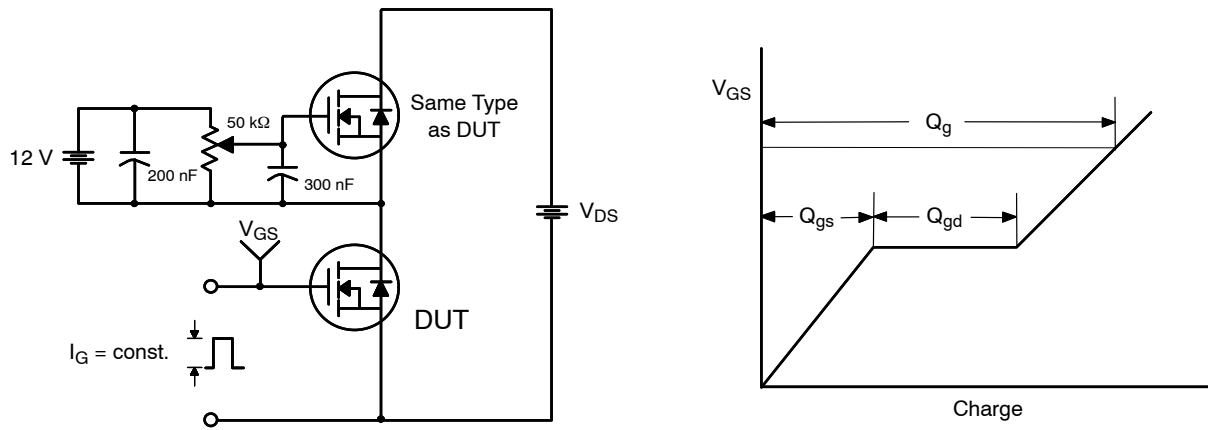


Figure 14. Gate Charge Test Circuit & Waveform

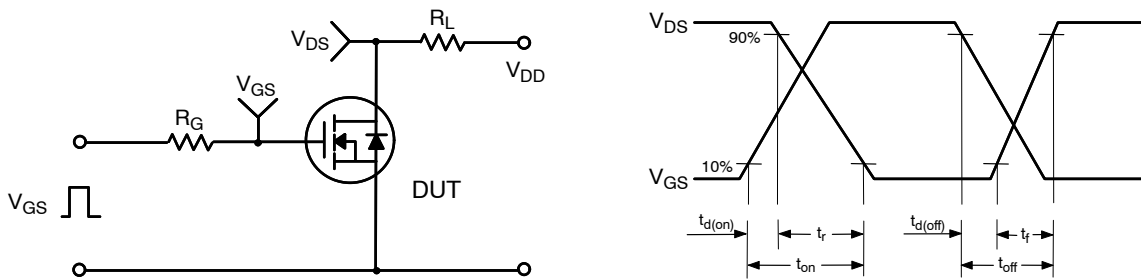


Figure 15. Resistive Switching Test Circuit & Waveforms

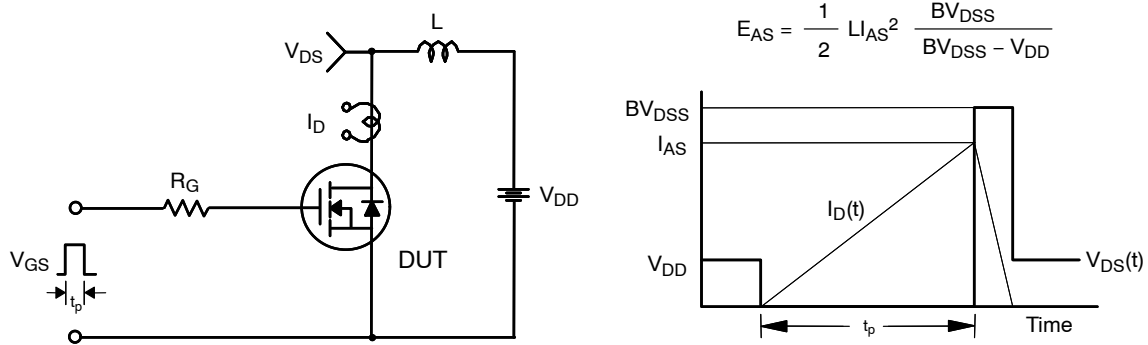


Figure 16. Unclamped Inductive Switching Test Circuit & Waveforms

FQP3N80C, FQPF3N80C

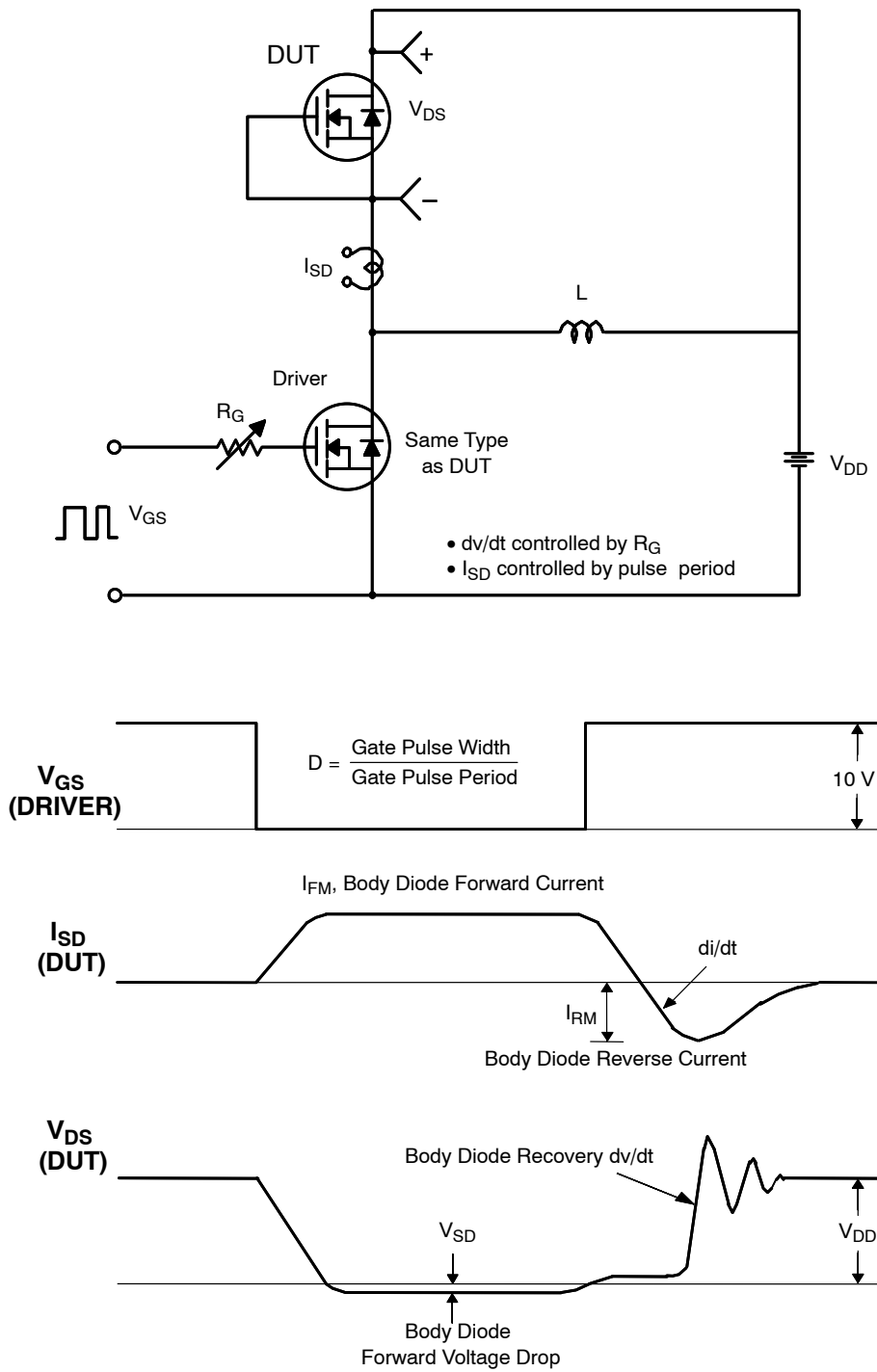


Figure 17. Peak Diode Recovery dv/dt Test Circuit & Waveforms

TO-220 Fullpack, 3-Lead / TO-220F-3SG
CASE 221AT
ISSUE B

DATE 19 JAN 2021



Scale 1:1



OPTION1



DIM	MILLIMETERS		
	MIN	NOM	MAX
A	4.50	4.70	4.90
A1	2.56	2.76	2.96
A2	2.34	2.54	2.74
b	0.70	0.80	0.90
b2	~	~	1.47
c	0.45	0.50	0.60
D	15.67	15.87	16.07
D1	15.60	15.80	16.00
E	9.96	10.16	10.36
e	2.34	2.54	2.74
F	~	0.84	~
H1	6.48	6.68	6.88
L	12.78	12.98	13.18
L1	3.03	3.23	3.43
Ø P	2.98	3.18	3.38
Ø P1	~	1.00	~
Q	3.20	3.30	3.40

NOTES:

A. DIMENSION AND TOLERANCE AS ASME Y14.5-2009

B. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR PROTRUCTIONS.

C. OPTION 1 - WITH SUPPORT PIN HOLE

OPTION 2 - NO SUPPORT PIN HOLE

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DESCRIPTION:	TO-220 FULLPACK, 3-LEAD / TO-220F-3SG	PAGE 1 OF 1

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TO-220-3LD
CASE 340AT
ISSUE B

DATE 08 AUG 2022

DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	4.00	--	4.70
A1	SEE NOTE "F"		
A2	2.10	--	2.85
b	0.55	--	1.00
b2	1.10	--	1.62
b4	1.42	--	1.62
c	0.36	--	0.60
D	13.90	--	16.30
D1	8.13	--	9.40
D2	11.50	--	14.30
D3	15.42	--	16.51
E	9.65	--	10.67
E1	7.59	--	8.65
e	2.40	--	2.67
H1	6.06	--	6.69
L	12.70	--	14.04
L1	2.70	--	4.10
P	3.50	--	4.00
Q	2.50	--	3.40
z	2.13 REF		
z1	2.06 REF		
θ	3°	--	5°

IF PRESENT, SEE NOTE "D"

GENERIC
MARKING DIAGRAM*



XXXX = Specific Device Code
A = Assembly Location
Y = Year
WW = Work Week
ZZ = Assembly Lot Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.



NOTES:

- A) REFERENCE JEDEC, TO-220, VARIATION AB
- B) ALL DIMENSIONS ARE IN MILLIMETERS.
- C) DIMENSIONS COMMON TO ALL PACKAGE SUPPLIERS EXCEPT WHERE NOTED [].
- D) LOCATION OF MOLDED FEATURE MAY VARY (LOWER LEFT CORNER, LOWER CENTER AND CENTER OF THE PACKAGE)
- △ DOES NOT COMPLY JEDEC STANDARD VALUE.
- F) "A1" DIMENSIONS AS BELOW:
SINGLE GAUGE = 0.51 - 0.61
DUAL GAUGE = 1.10 - 1.45
- △ PRESENCE IS SUPPLIER DEPENDENT
- H) SUPPLIER DEPENDENT MOLD LOCKING HOLES IN HEATSINK.

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